

isc Silicon NPN Power Transistor

2SD1734

DESCRIPTION

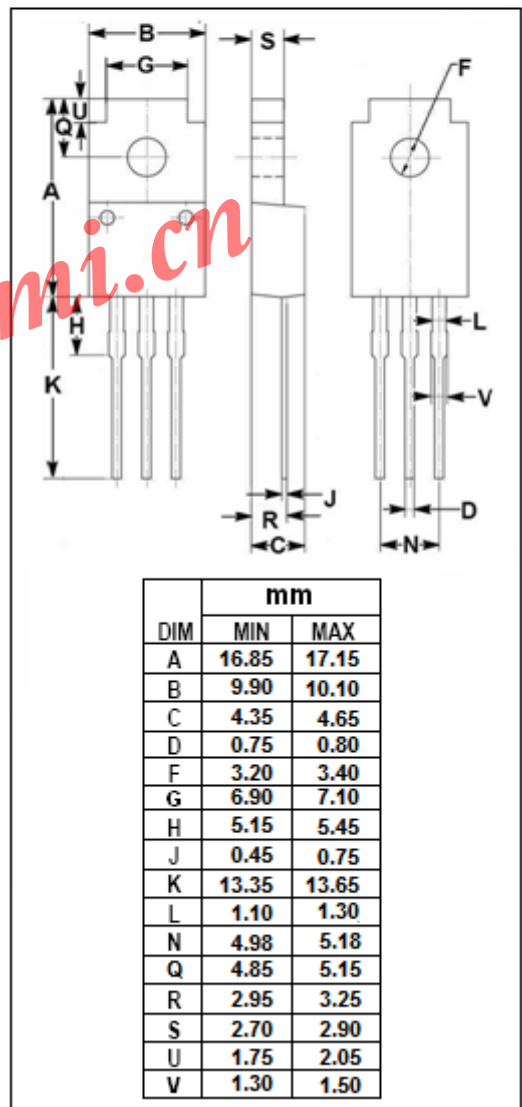
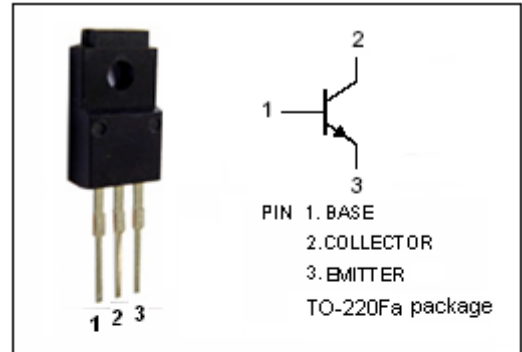
- High Voltage
- High Switching Speed
- Wide Area of Safe Operation

APPLICATIONS

- Designed for horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	1500	V
V <sub>CES</sub>	Collector-Emmitter Voltage	1500	V
V <sub>CEO</sub>	Collector-Emmitter Voltage	700	V
V <sub>EBO</sub>	Emmitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current-Continuous	1.5	A
I <sub>CP</sub>	Collector Current-Peak	5	A
I <sub>B</sub>	Base Current- Continuous	0.6	A
P <sub>C</sub>	Collector Power Dissipation @T <sub>C</sub> =25°C	40	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55-150	°C



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=500\text{mA}; I_C=0$	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.4\text{A}$			8.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.4\text{A}$			1.5	V
$h_{FE}$	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	6		30	
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=750\text{V}; I_E=0$			10	$\mu\text{A}$
		$V_{CB}=1500\text{V}; I_E=0$			1.0	mA
$f_T$	Transition Frequency	$I_C=0.5\text{A}; V_{CE}=10\text{V}$		2		MHz

## Switching Times, Resistive Load

$t_s$	Storage Time	$I_C=1\text{A}; I_{B1}=0.3\text{A}; I_{B2}=-0.6\text{A}; V_{CC}=200\text{V}$		1.0		$\mu\text{s}$
$t_f$	Fall Time			0.2		$\mu\text{s}$